onsemi

<u>Silicon Carbide (SiC)</u> <u>Schottky Diode</u> – EliteSiC, 20 A, 650 V, D2, TO-220-2L

FFSP2065B-F085

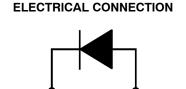
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 94 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

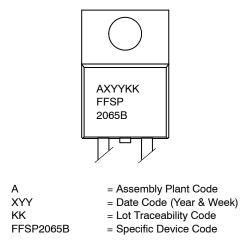
- Automotive HEV–EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



1. Cathode 2. Anode



MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSP2065B-F085	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		94	mJ
١ _F	Continuous Rectified Forward Current @ T _C	< 141°C	20	А
	Continuous Rectified Forward Current @ T _C	22.5		
1, 10100	Non-Repetitive Peak Forward Surge Cur- rent	T _C = 25°C, 10 μs	882	А
		T _C = 150°C, 10 μs	798	
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3 \text{ ms}$	84	A
P _{tot}	Power Dissipation	T _C = 25°C	150	W
		T _C = 150°C	25	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 94 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 19.4 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	1.0	°C/W

ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _F	Forward Voltage	$I_{F} = 20 \text{ A}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	1.38	1.7	V
		I _F = 20 A, T _C = 125°C	-	1.6	2.0	1
		I _F = 20 A, T _C = 175°C	-	1.72	2.4	1
I _R	Reverse Current	$V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	0.5	40	μΑ
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$	-	1	80	1
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$	-	2	160	1
Q_{C}	Total Capacitive Charge	V = 400 V	-	51	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	866	-	pF
		V _R = 200 V, f = 100 kHz	-	80	-	1
		V _R = 400 V, f = 100 kHz	-	70	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP2065B-F085	FFSP2065B	TO-220-2LD	Tube	N/A	N/A	50 Units

FFSP2065B-F085

TYPICAL CHARACTERISTICS TJ = 25°C UNLESS OTHERWISE NOTED

P_{TOT}, POWER DISSIPATION (W)

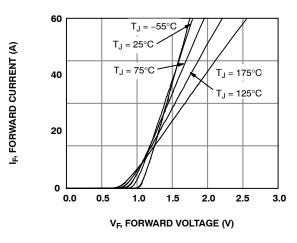


Figure 1. Forward Characteristics

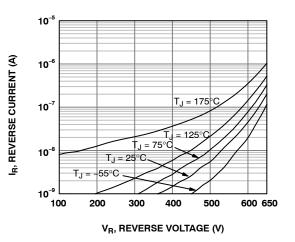


Figure 2. Reverse Characteristics

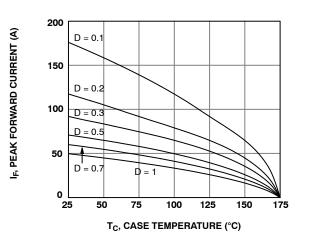
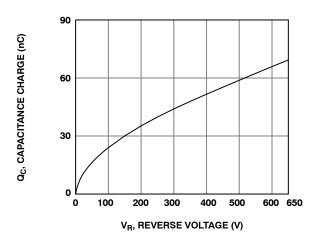


Figure 3. Current Derating





180 120 60 0 25 50 75 100 125 150 175 T_C, CASE TEMPERATURE (°C)

Figure 4. Power Dissipation

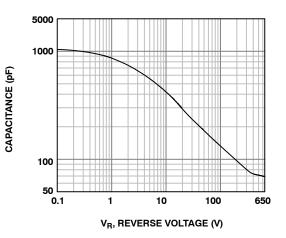
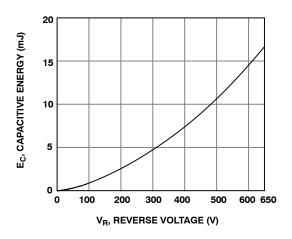
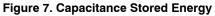


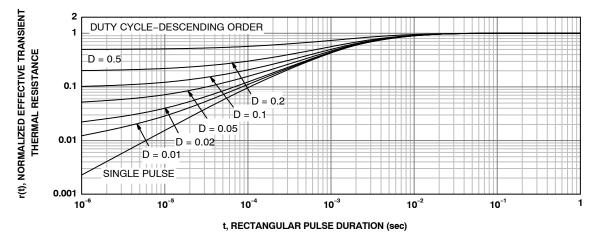
Figure 6. Capacitance vs. Reverse Voltage

FFSP2065B-F085

TYPICAL CHARACTERISTICS $T_J = 25^{\circ}C$ UNLESS OTHERWISE NOTED (CONTINUED)









TEST CIRCUIT AND WAVEFORMS

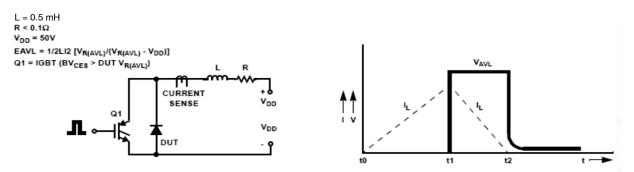
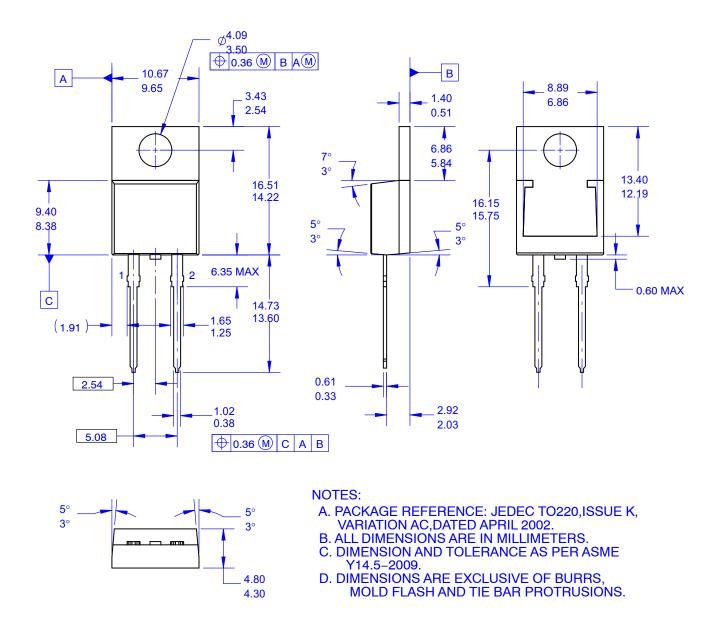


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

DATE 31 AUG 2016



DOCUMENT NUMBER:	98AON13832G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-220-2LD		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>